

CLAIMS:

1. A method of forming an aluminum comprising line having a titanium nitride comprising layer thereon, the method comprising:

forming a first layer comprising at least one of elemental aluminum or an aluminum alloy over a substrate;

forming a second layer comprising an alloy of titanium and the aluminum from the first layer, the alloy having a higher melting point than that of the first layer;

forming a third layer comprising titanium nitride over the second layer; and

forming the first, second and third layers into a conductive line.

2. The method of claim 1 wherein the titanium nitride of the third layer is formed in contact with the second layer.

3. The method of claim 1 wherein an outermost portion of the first layer is deposited at a temperature of at least about 400°C.

4. The method of claim 1 wherein an outermost portion of the first layer is deposited at a temperature of at least about 450°C.

5. The method of claim 1 comprising forming the second layer to have a thickness of from about 50 Angstroms to about 150 Angstroms.

1 6. The method of claim 1 comprising forming the second layer to  
2 have a thickness of from about 100 Angstroms to about 200 Angstroms.

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4 7. The method of claim 1 wherein temperature of at least an outer  
5 portion of the first layer is at least about 360°C during forming of the  
6 second layer.

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8 8. The method of claim 1 wherein temperature of at least an outer  
9 portion of the first layer is at least about 360°C during forming of the third  
10 layer.

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12 9. The method of claim 1 wherein the first layer consists essentially  
13 of elemental aluminum.  
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1 10. A method of forming an aluminum comprising line having a  
2 titanium nitride comprising layer thereon, the method comprising:

3 physical vapor depositing a first layer comprising at least one of  
4 elemental aluminum or an aluminum alloy over a substrate;

5 physical vapor depositing at least one of elemental titanium or a  
6 titanium alloy on the first layer and forming therefrom a second layer  
7 comprising an alloy of titanium and the aluminum from the first layer, the  
8 alloy having a higher melting point than that of the first layer;

9 physical vapor depositing a third layer comprising titanium nitride over  
10 the second layer; and

11 photopatterning the first, second and third layers into a conductive line.  
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13 11. The method of claim 10 wherein the titanium nitride of the third  
14 layer is deposited in contact with the second layer.

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16 12. The method of claim 10 wherein the second layer forms during  
17 the elemental titanium deposition.

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19 13. The method of claim 10 wherein essentially all the physical  
20 vapor deposited titanium alloys with the aluminum of the first layer.

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22 14. The method of claim 10 comprising physical vapor depositing  
23 each of the first layer, titanium, and third layer in different deposition  
24 chambers of the same processing tool.

1 15. The method of claim 10 comprising physical vapor depositing the  
2 titanium and third layer in the same deposition chamber.

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4 16. The method of claim 10 comprising physical vapor depositing the  
5 first layer in two different chambers of the same processing tool, and physical  
6 vapor depositing the titanium and third layer in a common chamber of the  
7 same processing tool.

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9 17. The method of claim 10 comprising physical vapor depositing the  
10 titanium and the third layer in the same deposition chamber without moving  
11 the substrate therefrom intermediate the titanium and third layer depositions.

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13 18. The method of claim 10 wherein an outermost portion of the  
14 first layer is deposited at a temperature of at least about 400°C.

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16 19. The method of claim 10 wherein an outermost portion of the  
17 first layer is deposited at a temperature of at least about 450°C.

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19 20. The method of claim 10 comprising depositing the second layer  
20 to have a thickness of from about 50 Angstroms to about 150 Angstroms.

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22 21. The method of claim 10 comprising depositing the second layer  
23 to have a thickness of from about 100 Angstroms to about 200 Angstroms.  
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1 27. A method of forming an aluminum comprising line having a  
2 titanium nitride comprising layer thereon, the method comprising:

3 in a processing tool, physical vapor depositing a first layer comprising  
4 at least one of elemental aluminum or an aluminum alloy over a substrate  
5 in a first chamber;

6 physical vapor depositing at least one of elemental titanium or a  
7 titanium alloy on the first layer in a second chamber of the processing tool  
8 while at least an outer portion of the first layer is at a temperature of at  
9 least about 360°C, and forming therefrom a second layer comprising an alloy  
10 of titanium and the aluminum from the first layer in the second chamber  
11 during said depositing, the alloy having a higher melting point than that of  
12 the first layer;

13 physical vapor depositing a third layer comprising titanium nitride on  
14 the second layer in the second chamber of the processing tool;

15 removing the substrate from the processing tool after depositing the  
16 third layer; and

17 photopatterning the first, second and third layers into a conductive line.  
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19 28. The method of claim 27 wherein essentially all the physical  
20 vapor deposited titanium alloys with the aluminum of the first layer.  
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22 29. The method of claim 27 comprising depositing the second layer  
23 to have a thickness of from about 50 Angstroms to about 150 Angstroms.  
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1 30. The method of claim 27 comprising depositing the second layer  
2 to have a thickness of from about 100 Angstroms to about 200 Angstroms.  
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4 31. The method of claim 27 wherein the first layer consists  
5 essentially of elemental aluminum, an aluminum alloy, or a mixture thereof.  
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7 32. The method of claim 27 wherein the first layer consists  
8 essentially of elemental aluminum.  
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10 33. The method of claim 27 wherein the physical vapor depositing  
11 at least one of elemental titanium or a titanium alloy comprises physical  
12 vapor depositing elemental titanium.  
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14 34. The method of claim 27 wherein temperature of at least an outer  
15 portion of the first layer is at least about 360°C during the physical vapor  
16 depositing of the third layer.  
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18 add A27  
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